### **ECH8656**

# ON Semiconductor®

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#### ON Ser

## N-Channel Power MOSFET 20V, 7.5A, 17mΩ, Dual ECH8

#### **Features**

- ON-resistance RDS(on)1=13m $\Omega$  (typ.)
- · Halogen free compliance
- · Protection diode in

- 1.8V drive
- · Nch + Nch MOSFET

#### **Specifications**

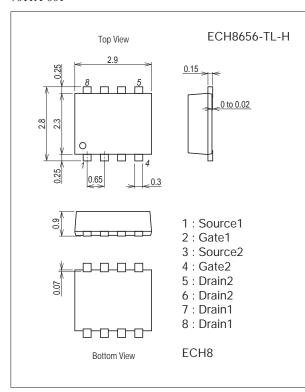
#### Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	VDSS		20	V
Gate-to-Source Voltage	V <sub>GSS</sub>		±10	V
Drain Current (DC)	ID		7.5	А
Drain Current (Pulse)	IDP	PW≤10μs, duty cycle≤1%	40	А
Allowable Power Dissipation	PD	When mounted on ceramic substrate (900mm <sup>2</sup> ×0.8mm) 1unit	1.3	W
Total Dissipation	PT	When mounted on ceramic substrate (900mm <sup>2</sup> ×0.8mm)	1.5	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

#### **Package Dimensions**

unit : mm (typ) 7011A-001



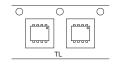
#### **Product & Package Information**

• Package : ECH8

• JEITA, JEDEC :-

• Minimum Packing Quantity : 3,000 pcs./reel

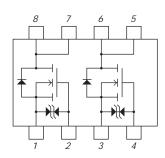
#### Packing Type: TL



#### Marking



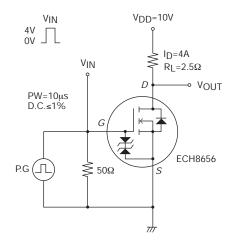
#### **Electrical Connection**



#### Electrical Characteristics at Ta=25°C

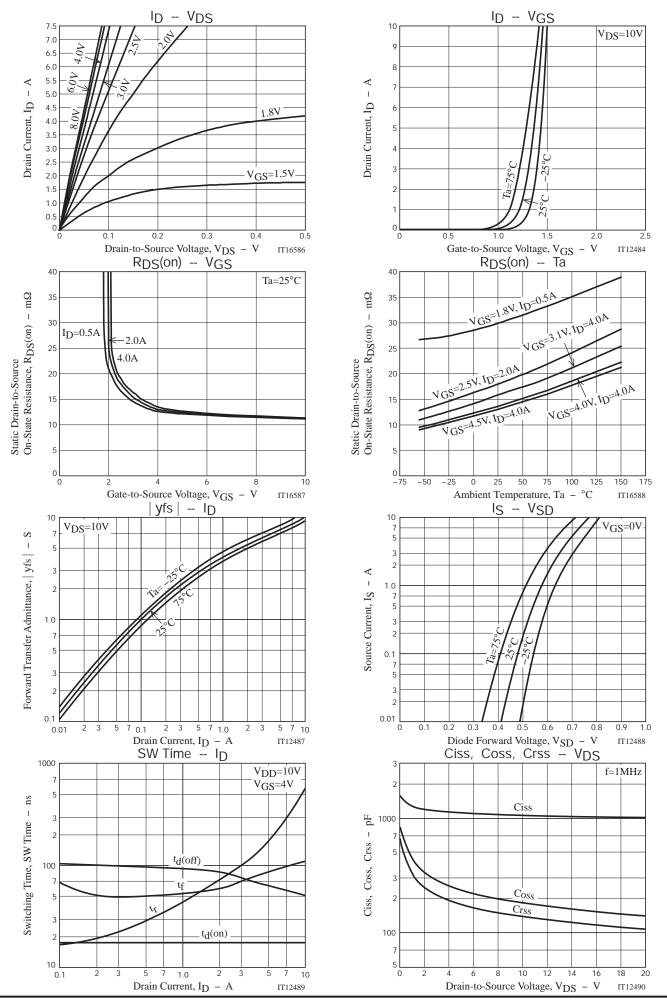
Parameter	Symbol	Conditions	Ratings			Unit	
Parameter	Symbol	Conditions	min	typ	max	Unit	
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=1mA, VGS=0V	20			V	
Zero-Gate Voltage Drain Current	IDSS	V <sub>DS</sub> =20V, V <sub>GS</sub> =0V			1	μΑ	
Gate-to-Source Leakage Current	IGSS	V <sub>GS</sub> =±8V, V <sub>DS</sub> =0V			±10	μΑ	
Cutoff Voltage	V <sub>GS</sub> (off)	V <sub>DS</sub> =10V, I <sub>D</sub> =1mA	0.5		1.3	V	
Forward Transfer Admittance	yfs	V <sub>DS</sub> =10V, I <sub>D</sub> =4A		7		S	
Static Drain-to-Source On-State Resistance	R <sub>DS</sub> (on)1	I <sub>D</sub> =4A, V <sub>G</sub> S=4.5V	9	13	17	mΩ	
	R <sub>DS</sub> (on)2	I <sub>D</sub> =4A, V <sub>G</sub> S=4.0V	9.4	13.5	18	mΩ	
	R <sub>DS</sub> (on)3	I <sub>D</sub> =4A, V <sub>G</sub> S=3.1V	11	16	22	mΩ	
	RDS(on)4	ID=2A, VGS=2.5V	12.5	18	26	mΩ	
	RDS(on)5	ID=0.5A, VGS=1.8V	17	30	48	mΩ	
Input Capacitance	Ciss			1060		pF	
Output Capacitance	Coss	V <sub>DS</sub> =10V, f=1MHz		180		pF	
Reverse Transfer Capacitance	Crss			135		pF	
Turn-ON Delay Time	t <sub>d</sub> (on)			17.5		ns	
Rise Time	t <sub>r</sub>			120		ns	
Turn-OFF Delay Time	t <sub>d</sub> (off)	See specified Test Circuit.		68		ns	
Fall Time	tf			80		ns	
Total Gate Charge	Qg			10.8		nC	
Gate-to-Source Charge	Qgs	V <sub>DS</sub> =10V, V <sub>GS</sub> =4.5V, I <sub>D</sub> =7.5A		2.1		nC	
Gate-to-Drain "Miller" Charge	Qgd			2.9		nC	
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =7.5A, V <sub>GS</sub> =0V		0.74	1.2	V	

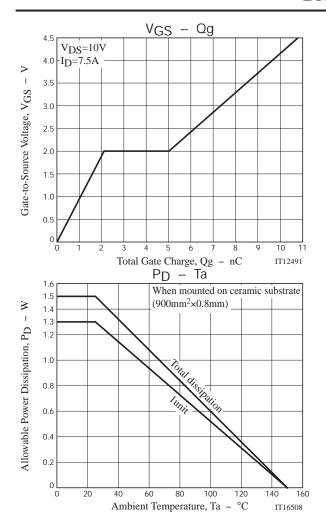
#### Switching Time Test Circuit

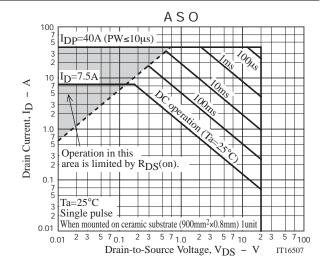


#### **Ordering Information**

Device	Package	Shipping	memo	
ECH8656-TL-H	ECH8	3,000pcs./reel	Pb Free and Halogen Free	





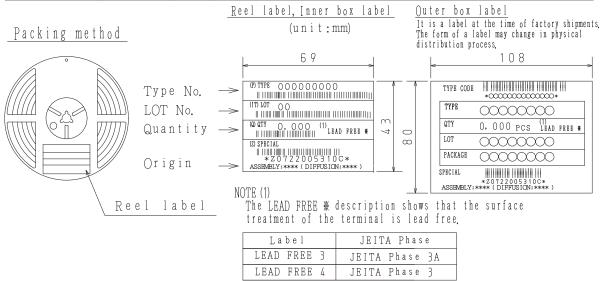


#### **Embossed Taping Specification**

#### ECH8656-TL-H

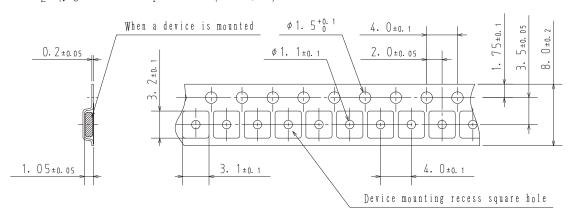
#### 1. Packing Format

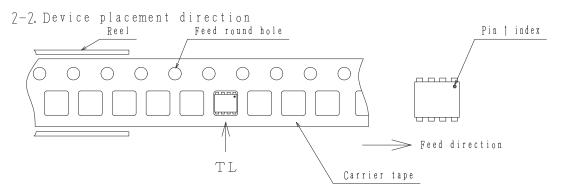
Package Name	Carrier Tape	Maximum Number of devices contained (pcs)			Packing	ng format		
	Туре	Reel	Inner box	Outer box	Inner $BOX(C-1)$	Outer BOX (A-7)		
ECH8	СРН6	3, 000	15, 000	90,000	5 reels contained	6 inner boxes contained		
					Dimensions:mm (external)	Dimensions:mm (external)		
					183×72×185	440×195×210		



#### 2. Taping configuration

2-1. Carrier tape size (unit:mm)

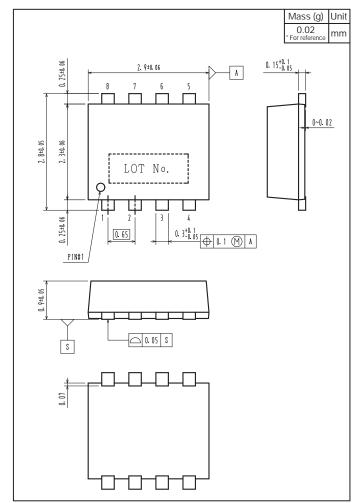




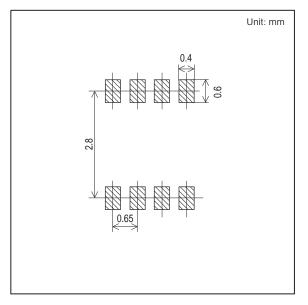
Those with pin 1 index on the feed hole side · · · · · TL

#### **Outline Drawing**

ECH8656-TL-H



#### **Land Pattern Example**



Note on usage: Since the ECH8656 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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